

Code: EC6T1

III B.Tech-II Semester–Regular/Supplementary Examinations–March 2019

**VLSI DESIGN
(ELECTRONICS & COMMUNICATION ENGINEERING)**

Duration: 3 hours

Max. Marks: 70

PART – A

Answer *all* the questions. All questions carry equal marks

11x 2 = 22 M

1.

- a) What is Latch – up in CMOS circuits?
- b) What is body effect? Which parameters are responsible for it?
- c) Draw a stick diagram of CMOS inverter.
- d) Define a buried contact and a butting contact of MOSFET.
- e) What is floor planning and placement in VLSI circuits?
- f) Distinguish pass transistor logic and Transmission gate logic.
- g) What is the difference between PLA and PAL?
- h) What is an ASIC? List out different types of ASICs.
- i) What is the difference between exhaustive and random test approaches?
- j) Write about stuck open and short faults.
- k) Draw the Layout encodings for NMOS and PMOS transistors.

PART – B

Answer any *THREE* questions. All questions carry equal marks.

3 x 16 = 48 M

2. a) Derive the expression for Drain to Source current in both Saturated and Non- saturated regions of MOS transistor. 8 M
- b) Explain the operation of enhancement mode MOSFET with neat diagrams. 8 M
3. a) Define standard unit of capacitance and calculate $\square C_g$ for 5 μm MOS circuits. 8 M
- b) Discuss briefly the λ – based design rules for layers, wires and transistors. 8 M
4. a) What are the limitations of Scaling. Derive the scaling factors for any two device parameters. 8 M
- b) Design a transmission gate based inverter logic and explain. 8 M
5. a) Discuss the differences between FPGAs and CPLDs. 8 M
- b) Design a Half-adder logic using programmable logic arrays. 8 M

6. a) What is the need for testing? Discuss different types of testing. 8 M
- b) Discuss scan based techniques of testing a design. 8 M